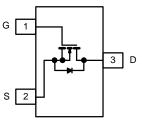


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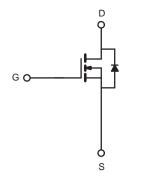
2N7002T-7-F-VB Datasheet N-Channel 60V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (mA)		
60	1.2 at V _{GS} = 10 V	330		









FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- Low On-Resistance: 2 Ω
- Low Threshold: 2 V (typ.)
- Low Input Capacitance: 25 pF
- Fast Switching Speed: 25 ns
- Low Input and Output Leakage
- Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

BENEFITS

- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

APPLICATIONS

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage	V _{GS}	± 20	v		
Continuous Drain Current (T_{l} = 150 °C) ^b	T _A = 25 °C	. I _D	330	mA	
Continuous Drain Current $(I_J = 150 {}^{\circ}\text{C})^2$	T _A = 100 °C		290		
Pulsed Drain Current ^a		I _{DM}	800		
	T _A = 25 °C	D	0.35	14/	
Power Dissipation ^b	T _A = 100 °C	PD	0.14	W	
Maximum Junction-to-Ambient ^b		R _{thJA}	350	°C/W	
Operating Junction and Storage Temperature Range		T _{J,} T _{stg}	- 55 to 150	°C	

Notes:

a. Pulse width limited by maximum junction temperature.

b. Surface Mounted on FR4 board.



COMPLIANT

9	B	®	Bs	sen	ni
W	ww.V	/Bs	em	i.co	m

			Limits				
Parameter	Symbol	Test Conditions	Min.	Min. Typ. ^a Max.		Unit	
Static			•	•	•		
Drain-Source Breakdown Voltage	V _{DS}	V_{DS} $V_{GS} = 0 V, I_D = 10 \mu A$				v	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1		2.5	v	
		$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 10		
		$V_{DS} = 0 V, V_{GS} = \pm 15 V$			1	μA	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 10 V$			± 150	nA	
		$V_{DS} = 0 V, V_{GS} = \pm 10 V, T_{J} = 85 °C$			± 1000		
		$V_{DS} = 0 V, V_{GS} = \pm 5 V$			± 100		
		V _{DS} = 60 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$			500	μA	
On-State Drain Current ^a	I _{D(on)}	V_{GS} = 10 V, V_{DS} = 7.5 V	800			<u> </u>	
		V_{GS} = 4.5 V, V_{DS} = 10 V	500			— mA	
	R _{DS(on)}	V _{GS} = 10 V, I _D = 500 mA		1.2		Ω	
Drain-Source On-Resistance ^a		V _{GS} = 4.5 V, I _D = 200 mA	2				
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 200 mA	100			mS	
Diode Forward Voltage	V _{SD}	I _S = 200 mA, V _{GS} = 0 V			1.3	V	
Dynamic ^a				1	I		
Total Gate Charge	Qg	V_{DS} = 10 V, V_{GS} = 4.5 V I _D \cong 250 mA		0.4	0.6	nC	
Input Capacitance	C _{iss}			30			
Output Capacitance	C _{oss}	$V_{\rm DS} = 25 \text{ V}, V_{\rm GS} = 0 \text{ V}$		6		pF	
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		2.5		1	
Switching ^{a, b, c}							
Turn-On Time	t _{d(on)}	V _{DD} = 30 V, R _I = 150 Ω			25		
Turn-Off Time	t _{d(off)}	$I_D \cong 200 \text{ mA}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{G}} = 10 \Omega$			35	ns	

Notes:

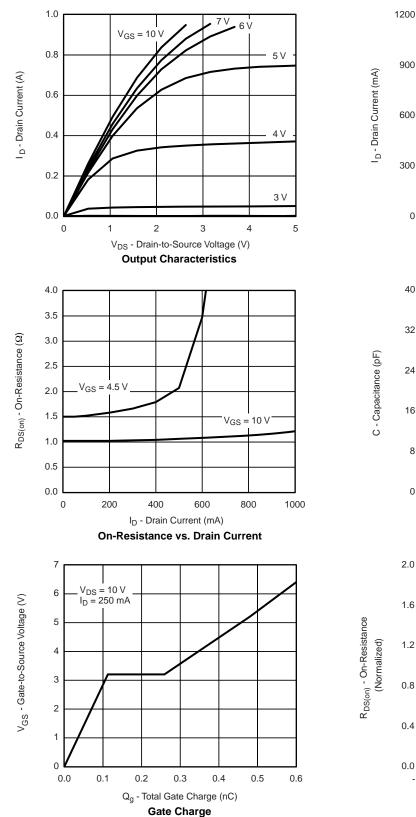
a. For DESIGN AID ONLY, not subject to production testing.

b. Pulse test: PW \leq 300 µs duty cycle \leq 2 %.

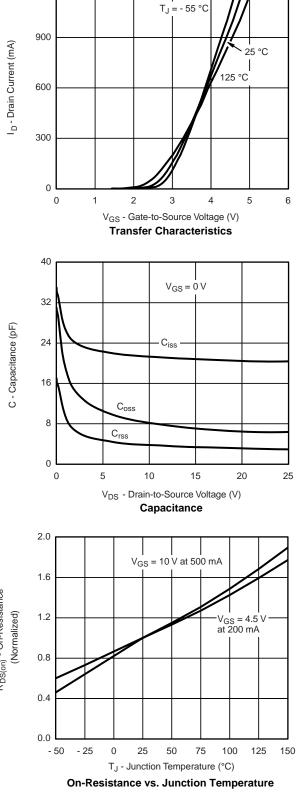
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



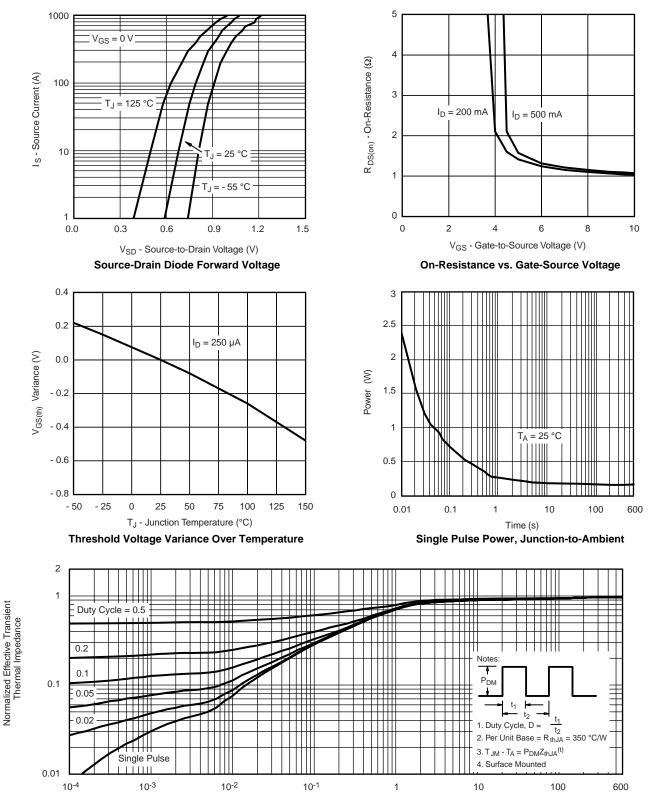


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



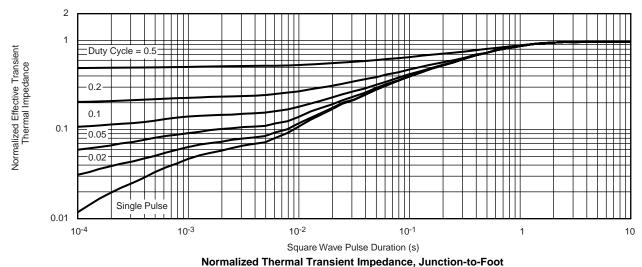


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



2N7002T-7-F-VB





THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

Note

The characteristics shown in the two graphs

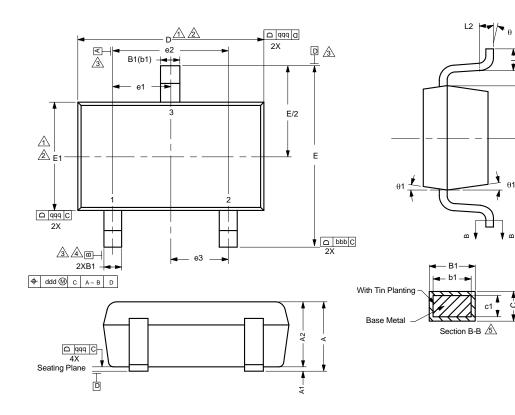
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SC-75A: 3 Leads



Notes

Dimensions in millimeters will govern.

- Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
- Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interelead flash, but including any mismatch between the top and bottom of the plastic body.

 $\underline{3}$ Datums A, B and D to be determined 0.10 mm from the lead tip.

4. Terminal positions are shown for reference only.

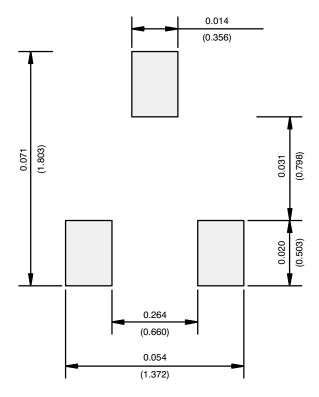
 $\frac{1}{2}$ These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES		
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.10		

DIM.	n in the second s			
DIM.	MIN.	NOM.	MAX.	NOTE
А	-	-	0.80	
A ₁	0.00	-	0.10	
A ₂	0.65	0.70	0.80	
B ₁	0.19	-	0.24	5
b ₁	0.17	-	0.21	
С	0.13	-	0.15	5
C1	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E1	0.66	0.76	0.86	1, 2
e ₁		0.50 BSC		
e ₂		1.00 BSC		
e ₃		0.50 BSC		
L	0.15	0.205	0.30	
L ₁	0.40 ref.			
L ₂	0.15 BSC			
θ	0°	-	8°	
θ_1	4°	-	10°	



RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

.



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